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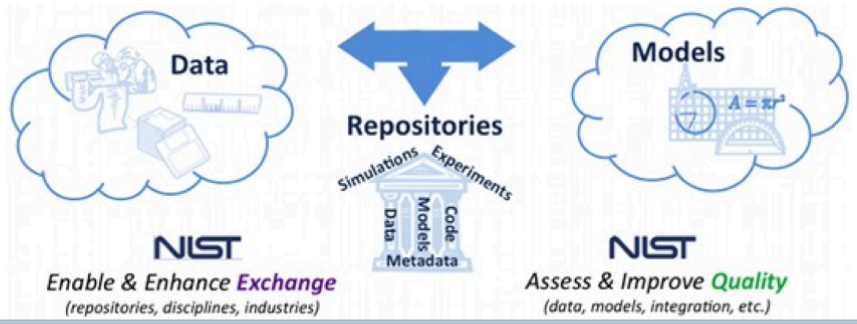

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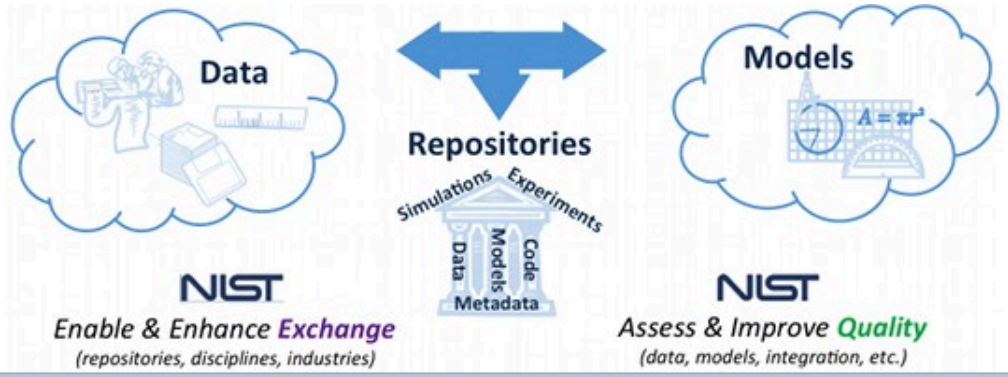

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Study of Si self-diffusion by nuclear techniques

Demond, F. J.; Kalbitzer, S.; Mannsperger, H.; Damjantschitsch, H. (2014-02-10)

By using ion implantation for preparation and p, γ-reactions for analysis of 30Si profiles the Si self-diffusion has been studied in the temperature range of 830–1200°C. The results reveal unambiguously that the diffusion ...

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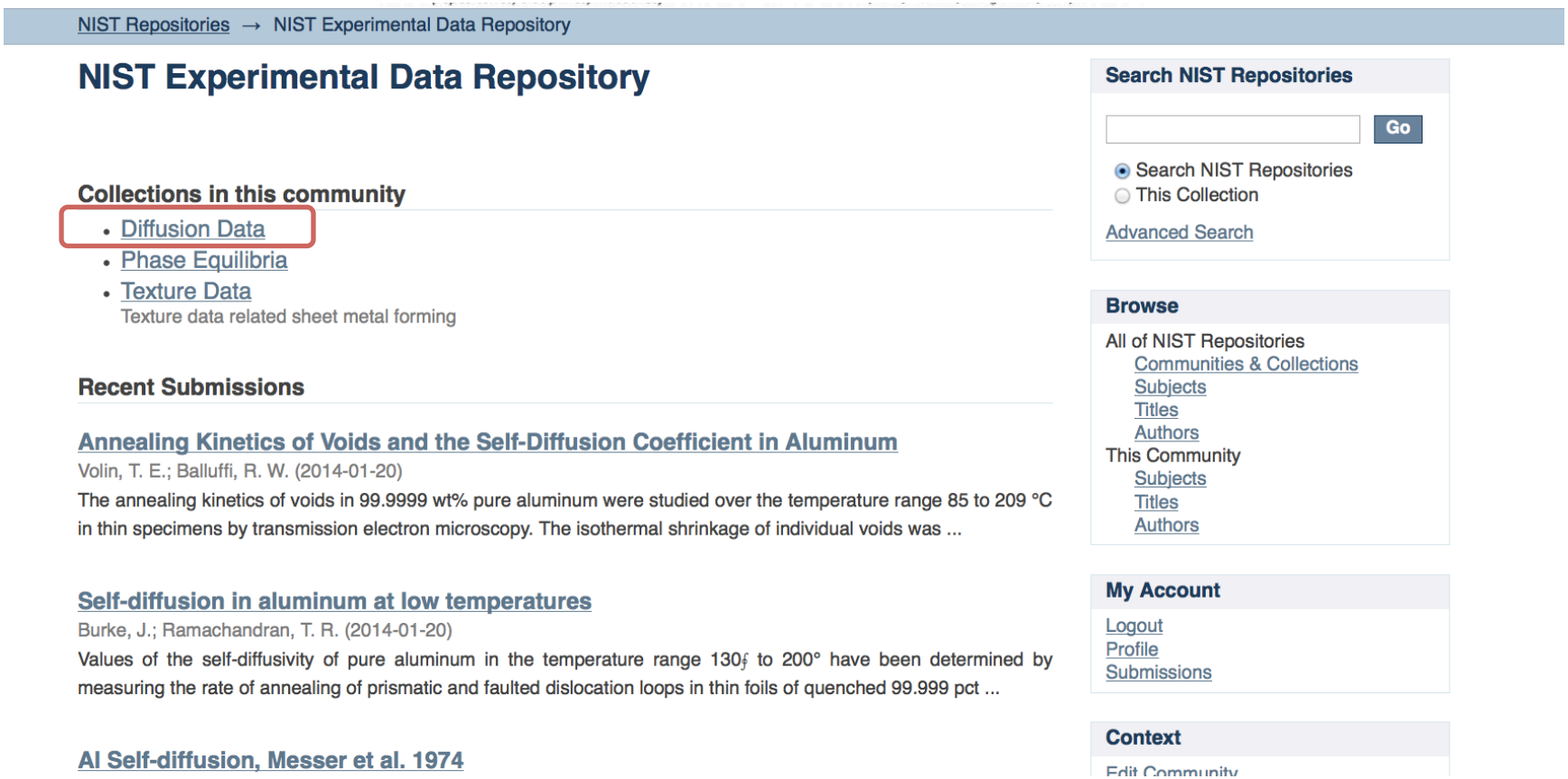

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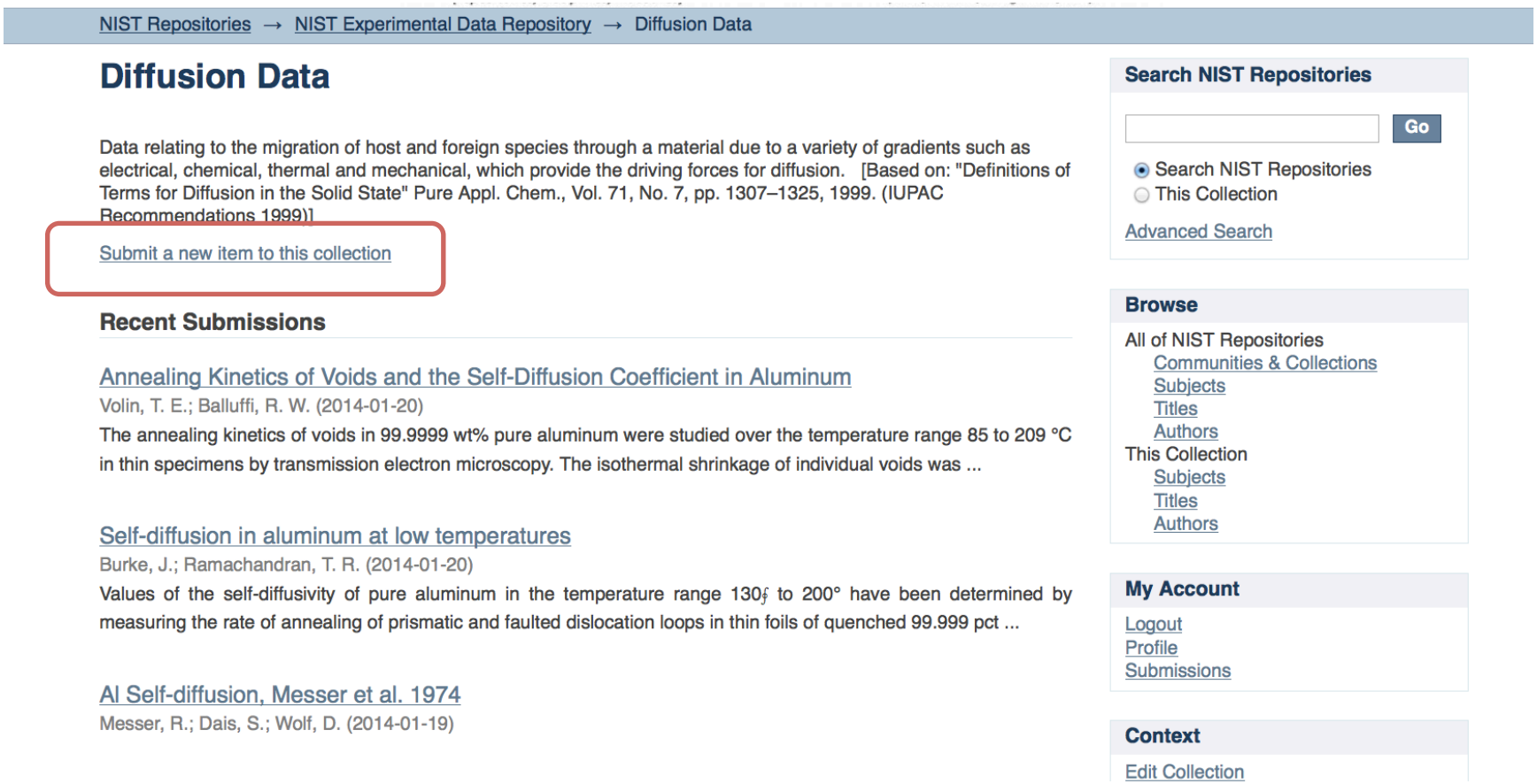

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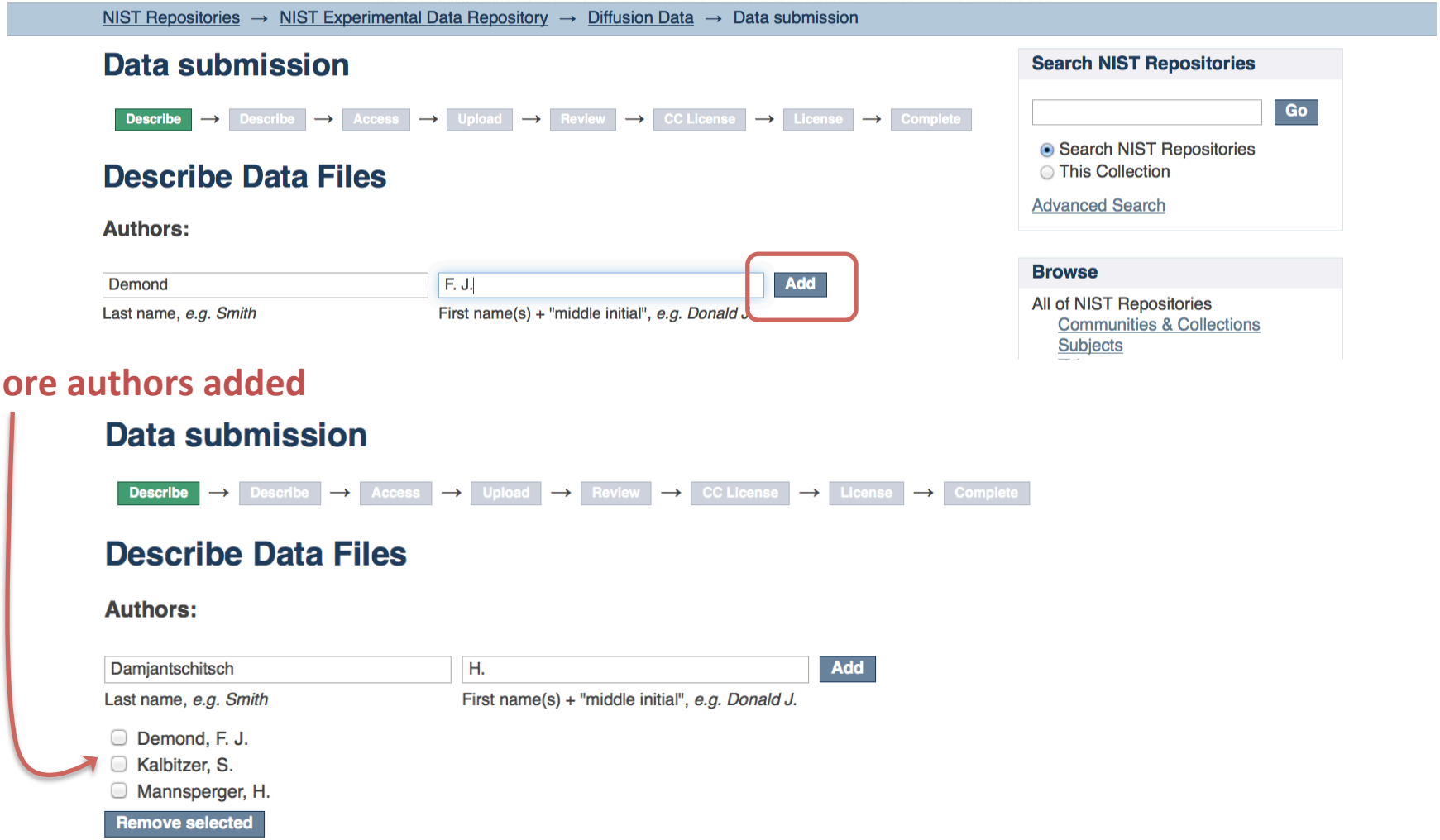

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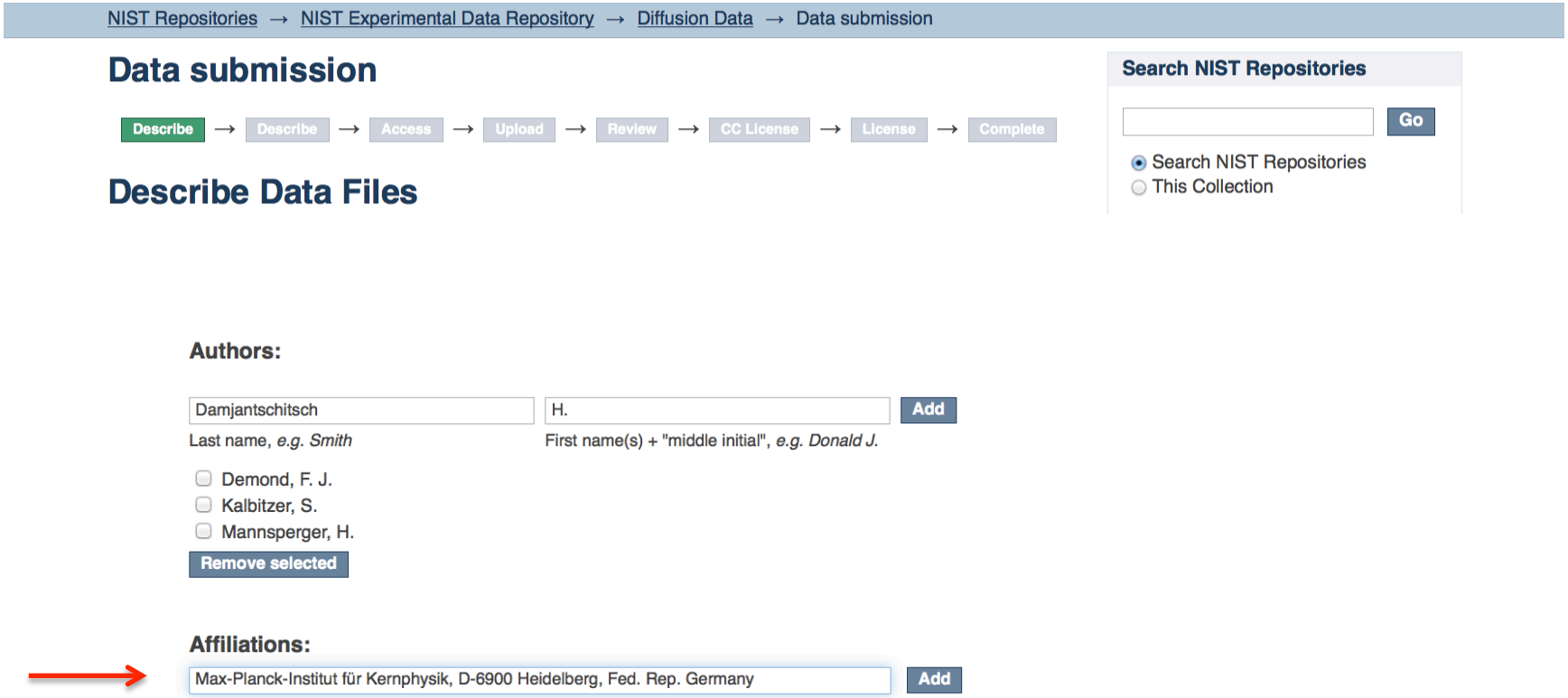

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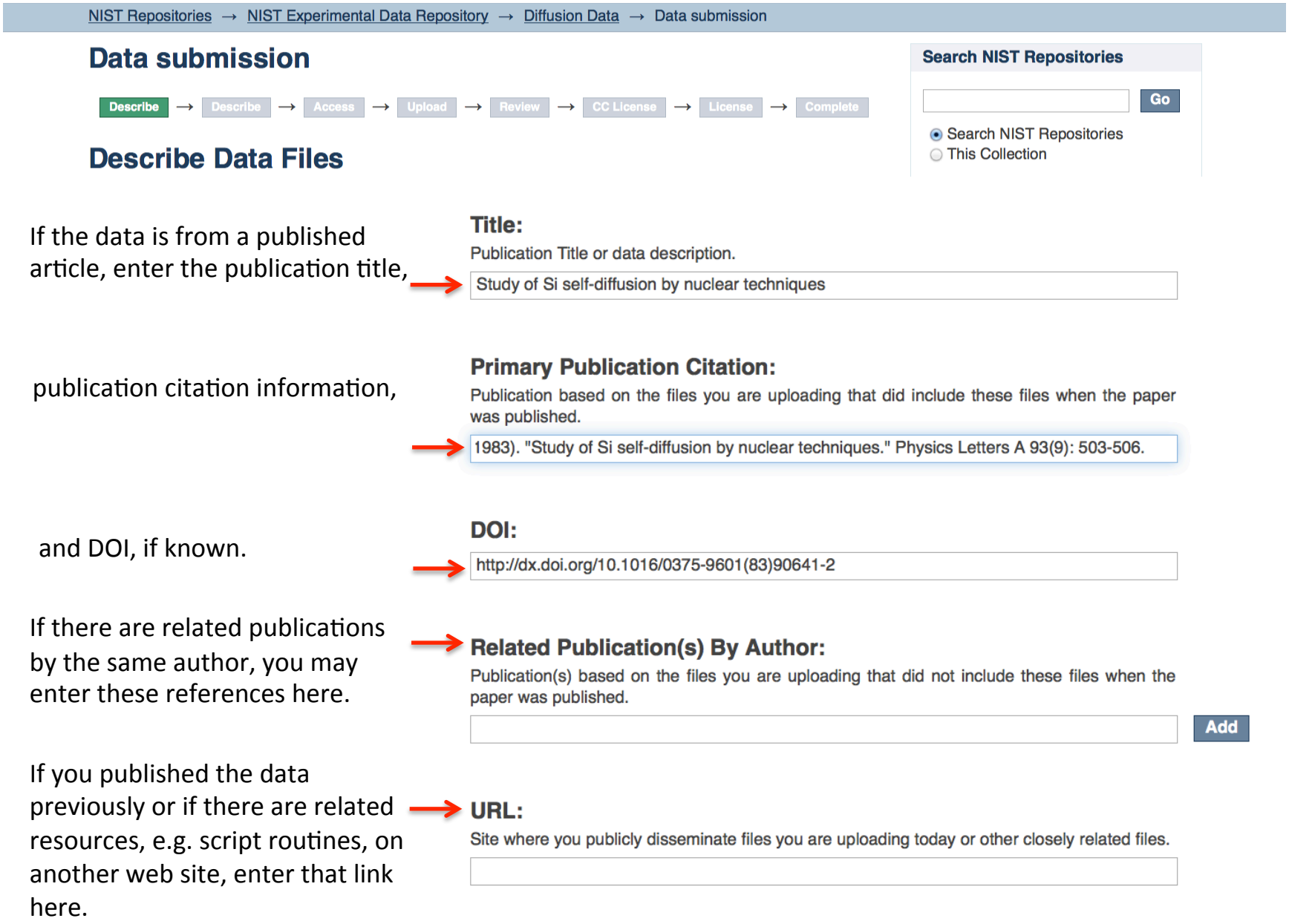

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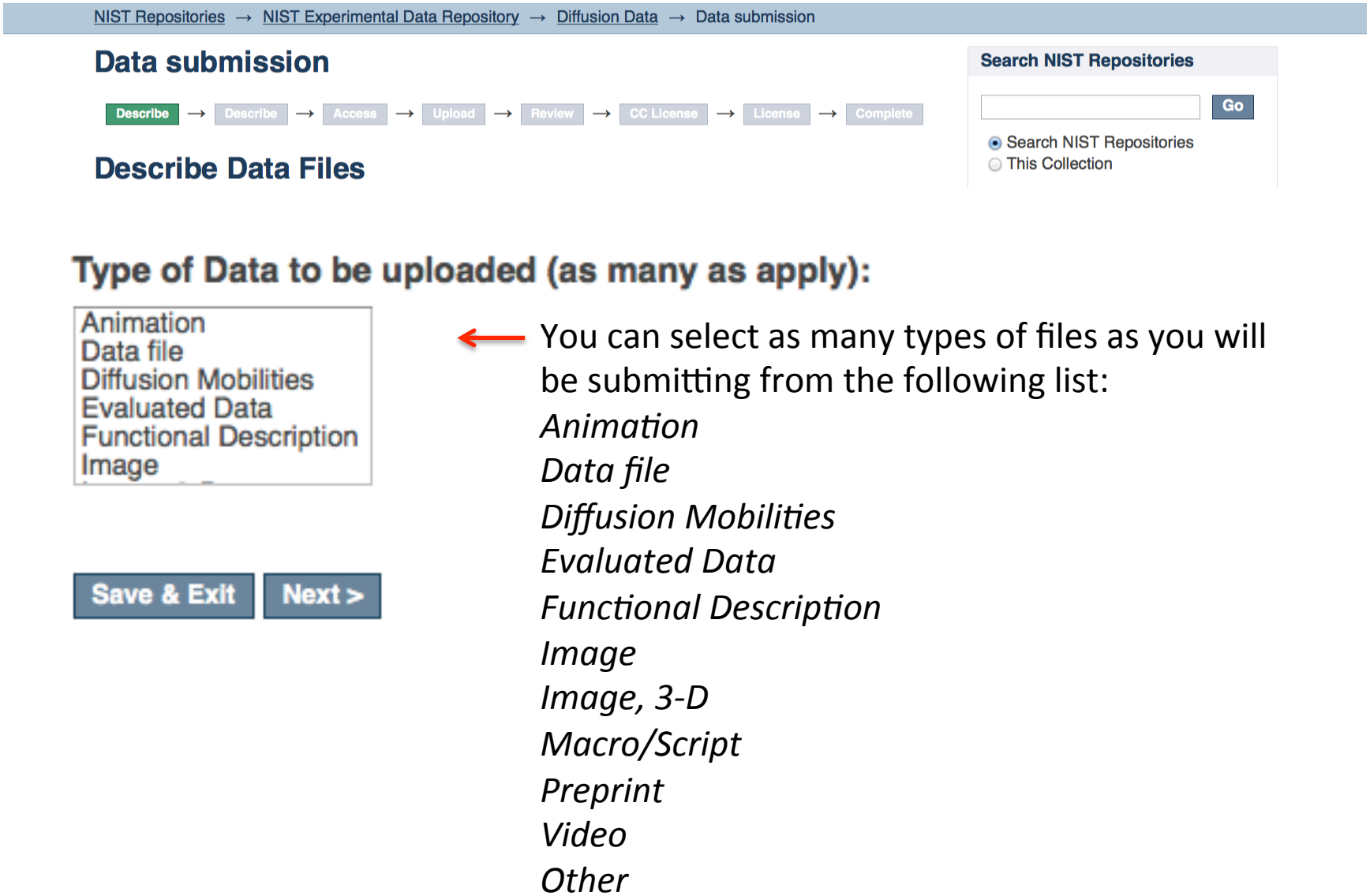

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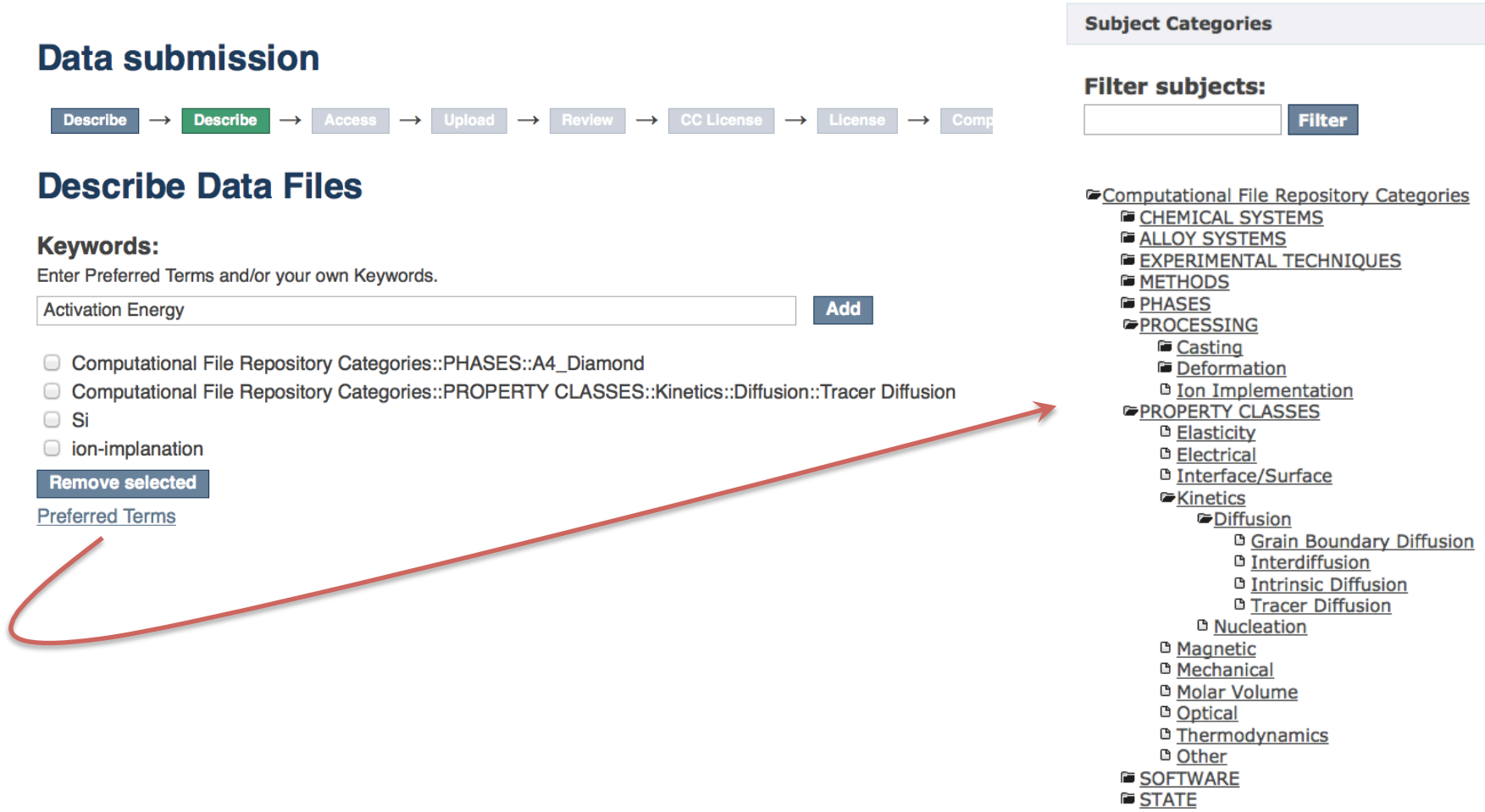

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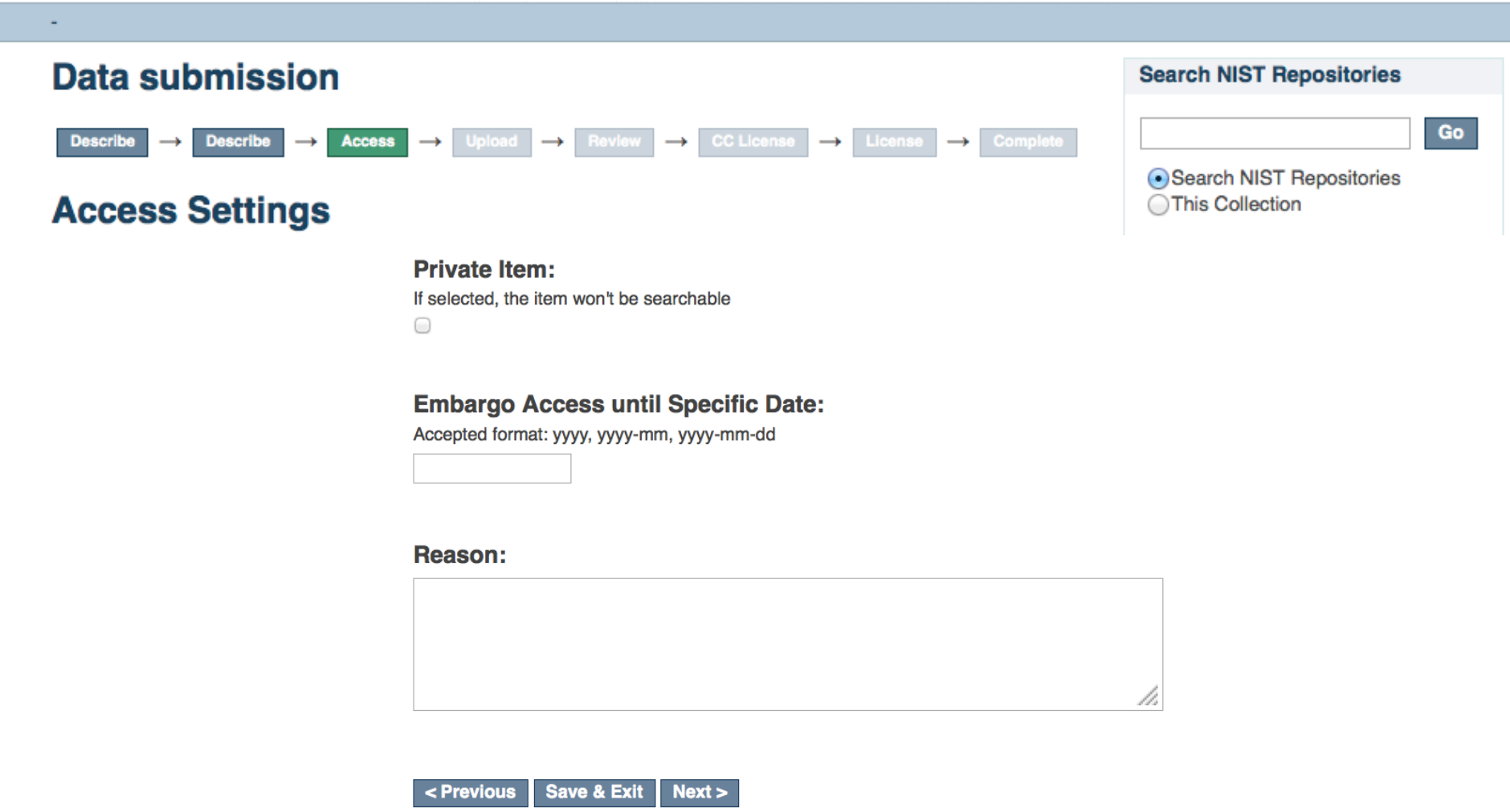

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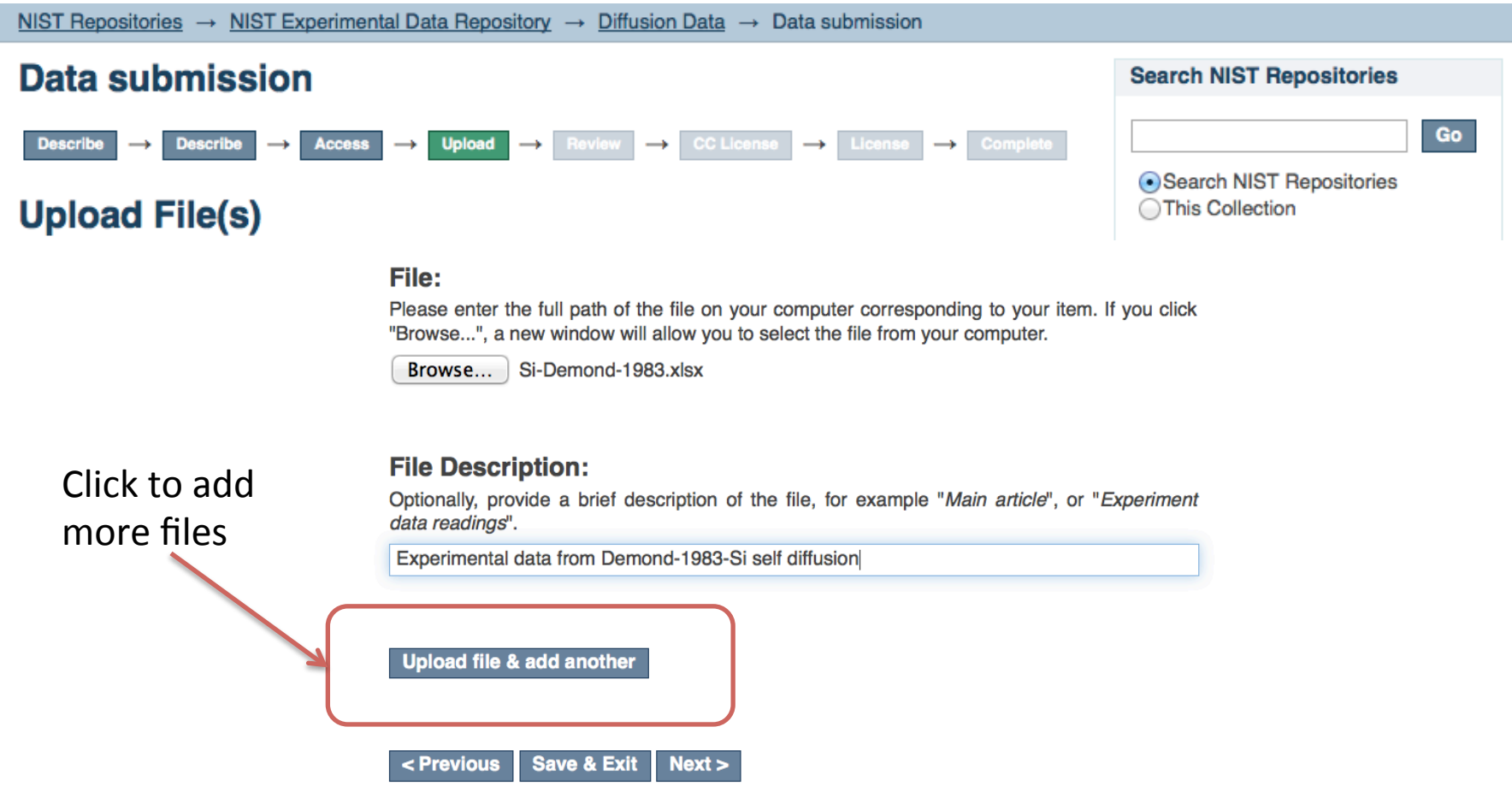

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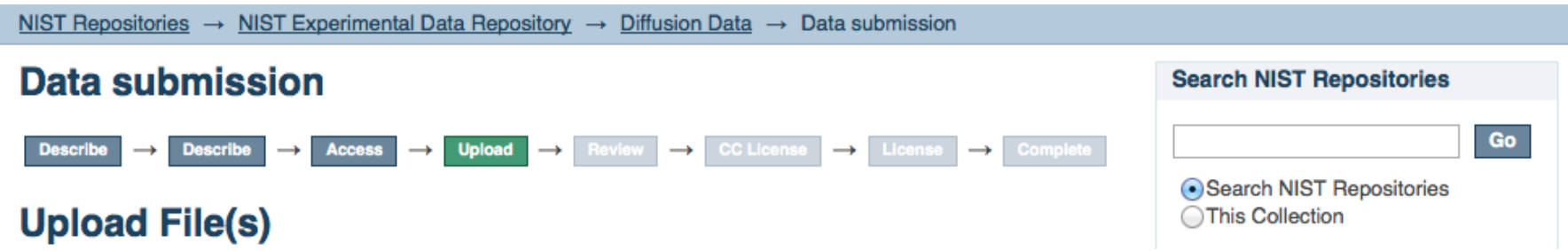

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Authors:
Demond, F. J.

Authors:
Kalbitzer, S.

Authors:
Mannsperger, H.

Authors:
Damjantschitsch, H.

Affiliations:
Max-Planck-Institut für Kernphysik, D-6900 Heidelberg, Fed. Rep. Germany

Contact Email:
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Title:
Study of Si self-diffusion by nuclear techniques

Primary Publication Citation:
Demond, F. J., et al. (1983). "Study of Si self-diffusion by nuclear techniques." Physics Letters A 93(9): 503-506.

DOI:
http://dx.doi.org/10.1016/0375-9601(83)90641-2

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Abstract:
By using ion implantation for preparation and p, γ-reactions for analysis of 30Si profiles the Si self-diffusion has been studied in the temperature range of 830–1200°C. The results reveal unambiguously that the diffusion process at the lower temperatures is characterized by parameters substantially smaller than those reported for the high-temperature regime.

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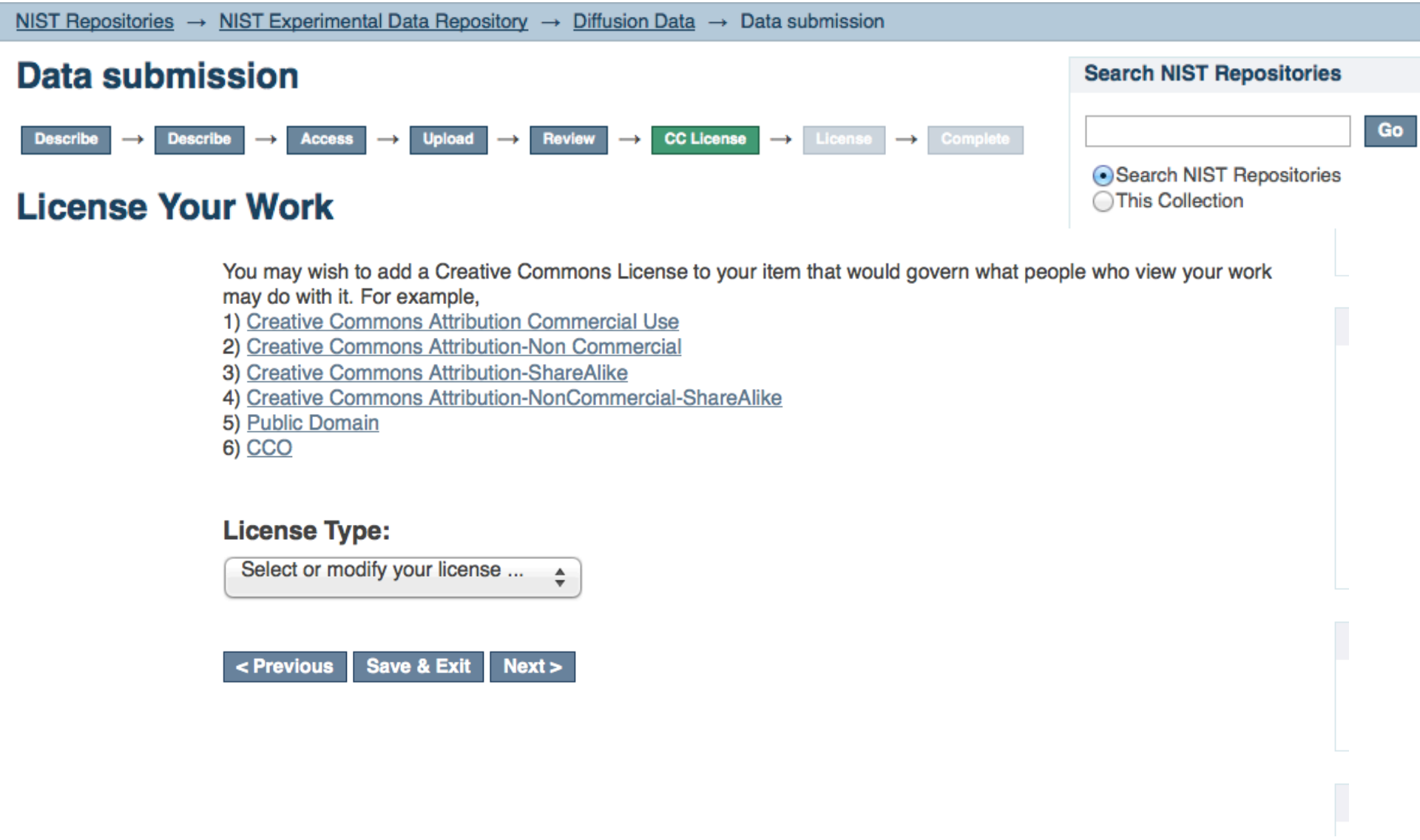

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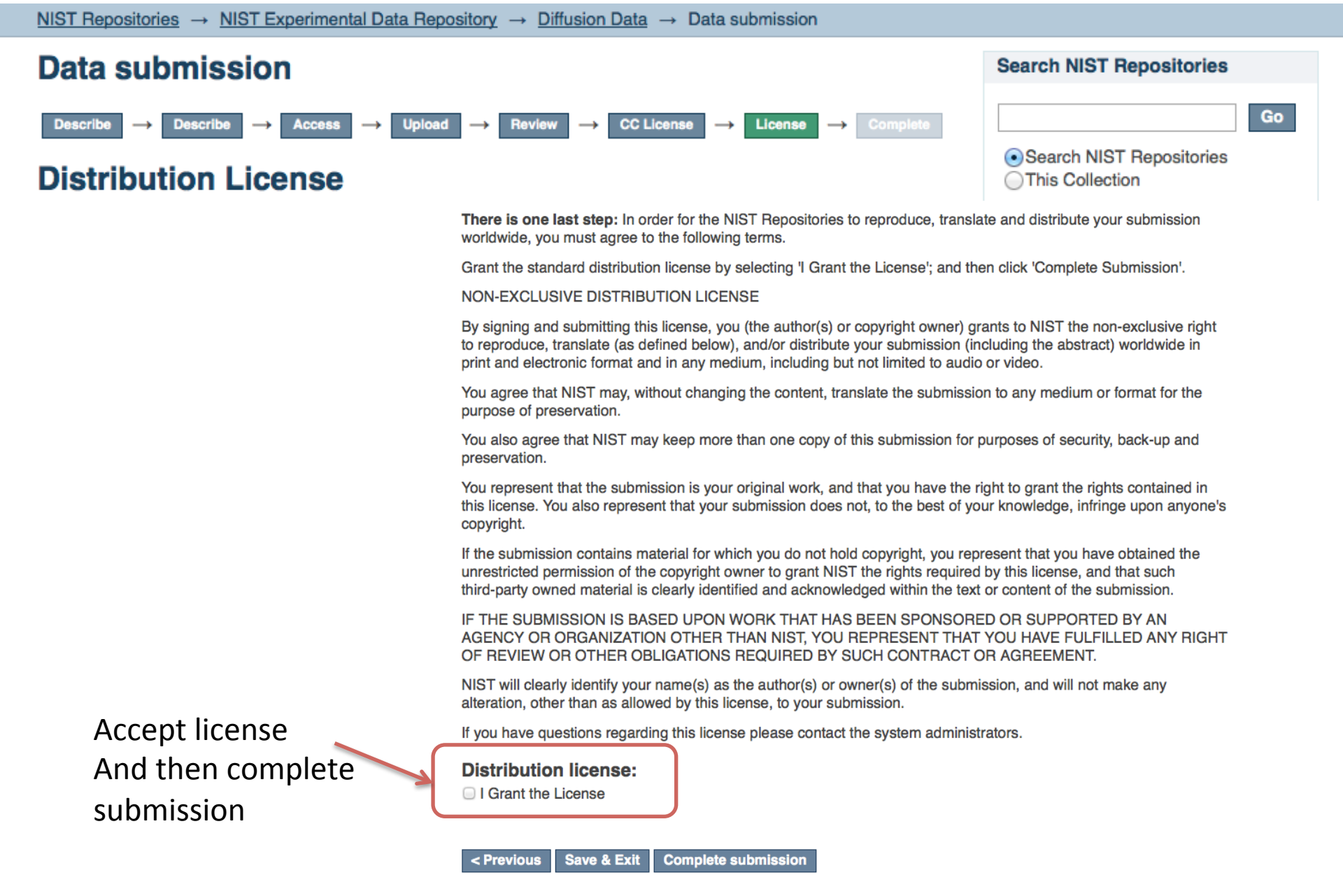

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Affiliation: Max-Planck-Institut für Kernphysik, D-6900 Heidelberg, Fed. Rep. Germany
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